

In the Claims:

Please cancel claims 1-24 without any disclaimer or a prejudice, amend claim 25, and add a new claim 35 as follows. Listings of the pending claims are as follows:

1-24 (Cancelled)

25. (Currently Amended) A method ~~of~~ for fabricating a liquid crystal display, comprising the steps of:

forming a bottom substrate ~~such that the bottom substrate has~~ that has a first region where liquid crystal molecules bear a first pretilt angle, and a second region where liquid crystal molecules bear a second pretilt angle smaller than the first pretilt angle;

forming a top substrate ~~such that the top substrate~~ that faces the bottom substrate with liquid crystal molecules bearing a third pretilt angle, the third pretilt angle being medium between the first pretilt angle and the second pretilt angle; and

forming a liquid crystal layer ~~such that~~ where the liquid crystal layer is sandwiched between the bottom substrate and the top substrate with liquid crystal molecules, ~~the liquid crystal molecules being twisted at the first region in a first direction while being twisted at the second region in a second direction.~~

26. (Original) The method of claim 25, wherein the bottom substrate is formed through the steps of:

forming a gate wire, a data wire and a thin film transistor on a first insulating substrate such that the data wire crosses over the gate wire while being insulated from the gate wire, and the thin film transistors are electrically connected to the data wire; and

forming a pixel electrode such that the pixel electrode are electrically connected to the thin film transistor, each pixel electrode bearing a first surface roughness at the first region while bearing a second surface roughness at the second region, the second surface roughness being higher than the first surface roughness.

27. (Original) The method of claim 26, wherein the pixel electrode are formed through the steps of:

depositing a transparent conductive layer over the first substrate;

coating a photoresist film on the transparent conductive layer;

selectively exposing the photoresist film to light using a mask;

forming a photoresist pattern on the transparent conductive layer through developing the light-exposed photoresist film, the photoresist pattern having a first portion placed over the first region of the common electrode with a first thickness, and a second portion placed over the second region of the common electrode with a second thickness larger than the first thickness;

etching the transparent conductive layer using the photoresist pattern as a mask to form a shape of the pixel electrode;

removing the first portion of the photoresist pattern while exposing the underlying transparent conductive layer;

forming the first region of the pixel electrode through treating the surface of the exposed

portion of the transparent conductive layer; and

forming the second region of the pixel electrode through removing the second portion of the photoresist pattern.

28. (Original) The method of claim 27, wherein the surface is treated through bombarding inert gas on the exposed portion of the transparent conductive layer.

29. (Original) The method of claim 28 wherein the surface is treated through wet-etching the exposed portion of the transparent conductive layer using a wet etching solution.

30. (Original) The method of claim 25, wherein the step of forming the top substrate is made through forming a common electrode on a second insulating substrate such that the common electrode corresponding to the pixel electrode with a third surface roughness, the third surface roughness being medium between the first surface roughness and the second surface roughness.

31. (Original) The method of claim 30, wherein the common electrode is formed through the steps of:

depositing a transparent conductive layer over the second substrate; and

treating surface of the transparent conductive layer such that the transparent conductive layer bears the third surface roughness.

32. (Original) The method of claim 31, wherein the surface is treated through bombarding inert gas on the exposed portion of the transparent conductive layer.

33. (Original) The method of claim 32, wherein the surface is treated through wet-etching the exposed portion of the transparent conductive layer.

34. (Original) The method of claim 25, wherein the top substrate is formed through the steps of:
forming a common electrode over a second insulating substrate such that the common electrode corresponds the pixel electrode;
coating an alignment layer covering the common electrode; and
rubbing the alignment layer such that the liquid crystal molecules at the top substrate bear the third pretilt angle.

35. (Currently Added) The method of claim 25, wherein the liquid crystal molecules are twisted in a first direction at the first region, and the liquid crystal molecules are twisted in a second direction at the second region.